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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

Sheet 1 of 1

Application No.: 10/018,401  
Filing Date: December 19, 2001  
First Named Inventor: TRAN et al.  
Group Art Unit:  
Examiner Name:  
Attorney Docket No.: P07472US00/WEJ

**U.S. PATENT DOCUMENTS**

Exam. Initial	Document No. Number - Kind	Publication Date MM-DD-YYYY	Name Patentee or Applicant	Relevance Passages or Figures

**FOREIGN PATENT DOCUMENTS**

Exam. Initial	DOCUMENT Country-Number-Kind	Publication Date MM-DD-YYYY	Name Patentee or Applicant	Relevance Passages or Figures	Trans

**OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS**

Exam. Initial	Author Name (in CAPS), Title of Article/Item, Date, Page(s), Volume-Issue No., Publisher, City and/or Country where published	Trans
M>	DRUZ et al., "Growth Epitaxial Films of Sulfides of Cadmium and Zinc from Dithiocarbamate Compounds $M(S_2CNEt_2)_2$ ( $M=Cd, ZN$ )", Metalloorganischeskaia Khimiia, 1, No. 3, 1988, pp. 645-649.	No
M>	NOMURA et al., "Single-Source MOVPE Growth of Zinc Sulfide Thin Films Using Zinc Dithiocarbamate Complexes", Thin Solid Films, 271, 1995, pp. 4-7.	
M>	CHEON et al., "Gas Phase Photochemical Synthesis of II/VI Metal Sulfide Films...", Journal Of The American Chemical Society, 119, No. 16, 23 April 1997, pp. 3838-3839.	
M>	JONES et al., "The Growth of CdS and CdSe Alloys by MOCVD using a New Dimethylcadmium Adduct", Journal of Crystal Growth, 97, 1989, pp. 537-541.	
M>	Derwent Abstract Accession No. 96-496203/49, Class E12, RU 2055948 C1 (AS SIBE INORG CHEM INST), 10 March 1996.	
M>	Patent Abstract of Japan, JP 11087747 A (Matsushita Denchi Kogyo KK), 30 March 1999 & JP 11087747 A.	

Examiner Signature

Date Considered

3/24/2003

\* Examiner: Initial if considered, whether or not citation is in conformance with MPEP §609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

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